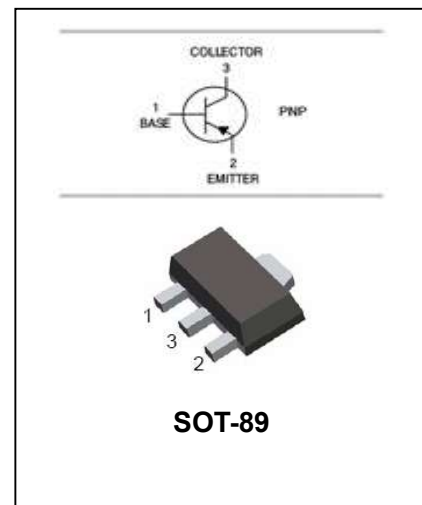


PNP Epitaxial Planar Silicon Transistors

2SB1119

FEATURES

- Very small size making it easy to provide High-density, small-size hybrid IC's.



ORDERING INFORMATION

Type No.	Marking	Package Code
2SB1119	BB	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -DC -Pulse	-1 -2	mA
P_C	Collector Dissipation	500	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

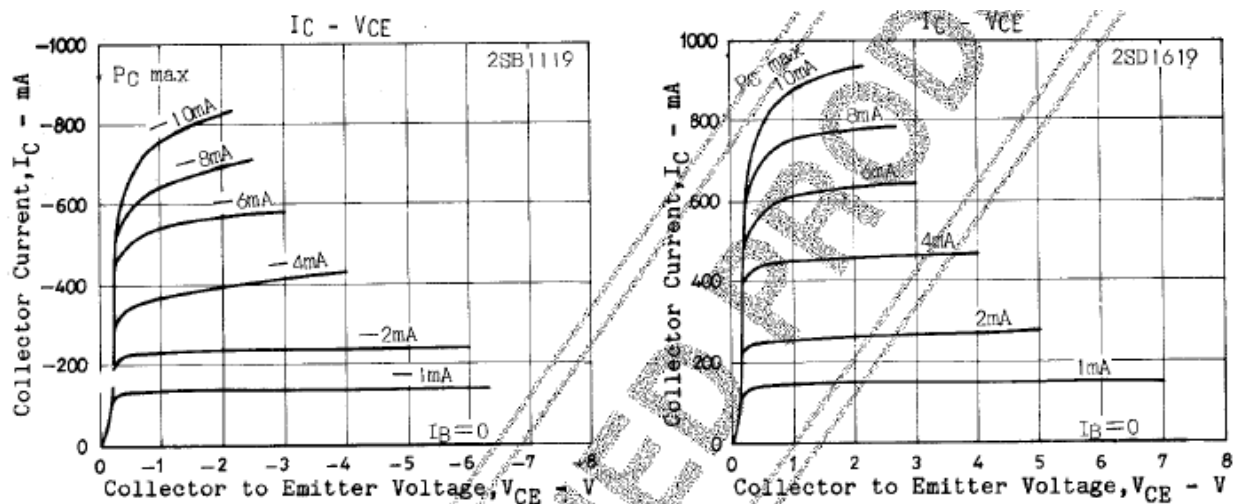
PNP Epitaxial Planar Silicon Transistors

2SB1119

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

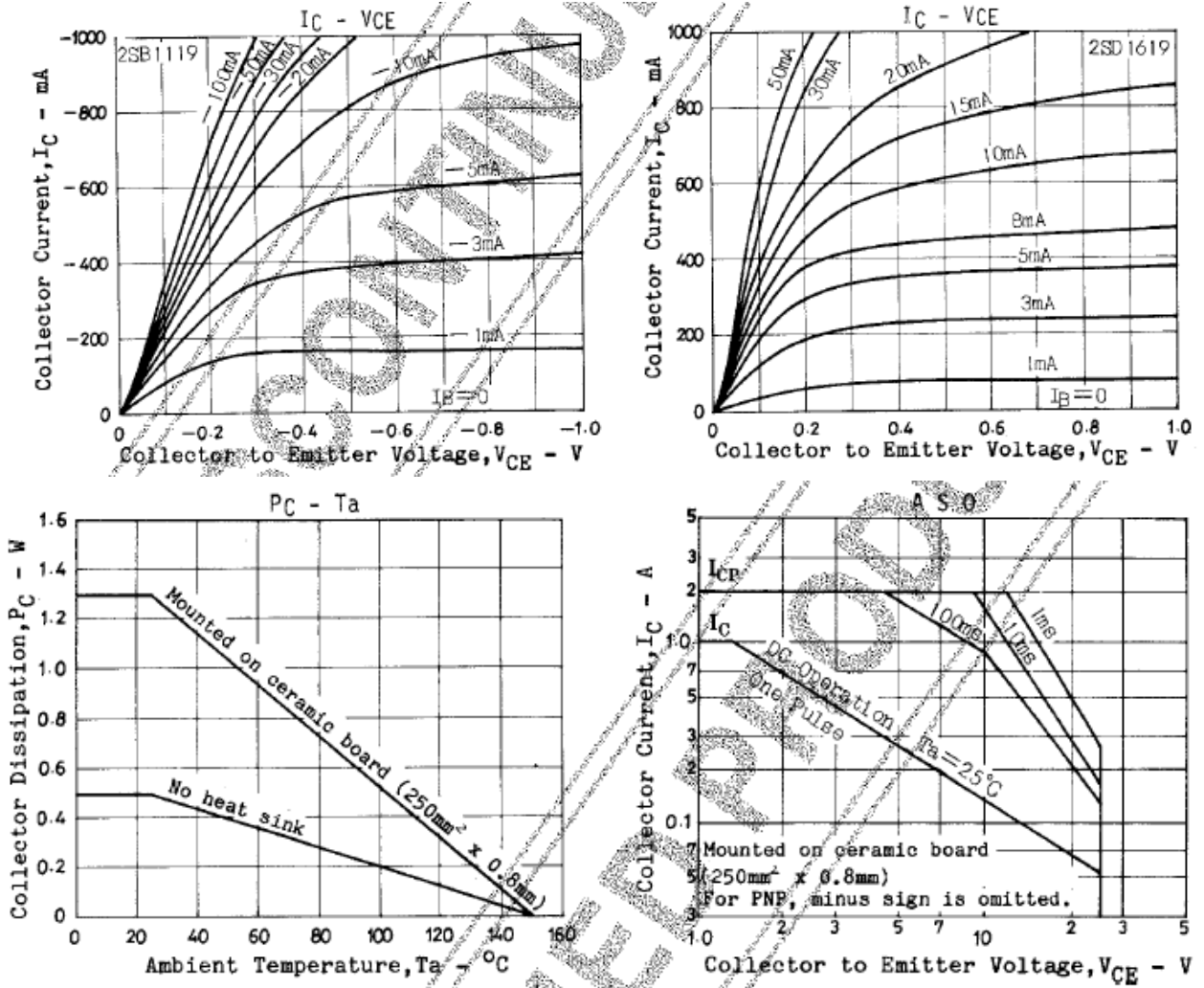
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	h_F	$V_{CE} = -2V, I_C = -50mA$ $V_{CE} = -2V, I_C = -1A$	100 40		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.1	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA,$		180		MHz
Output Capacitance	C_{obo}	$V_{CB} = -10V, f = 1.0MHz, I_E = 0$		15		pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



PNP Epitaxial Planar Silicon Transistors

2SB1119



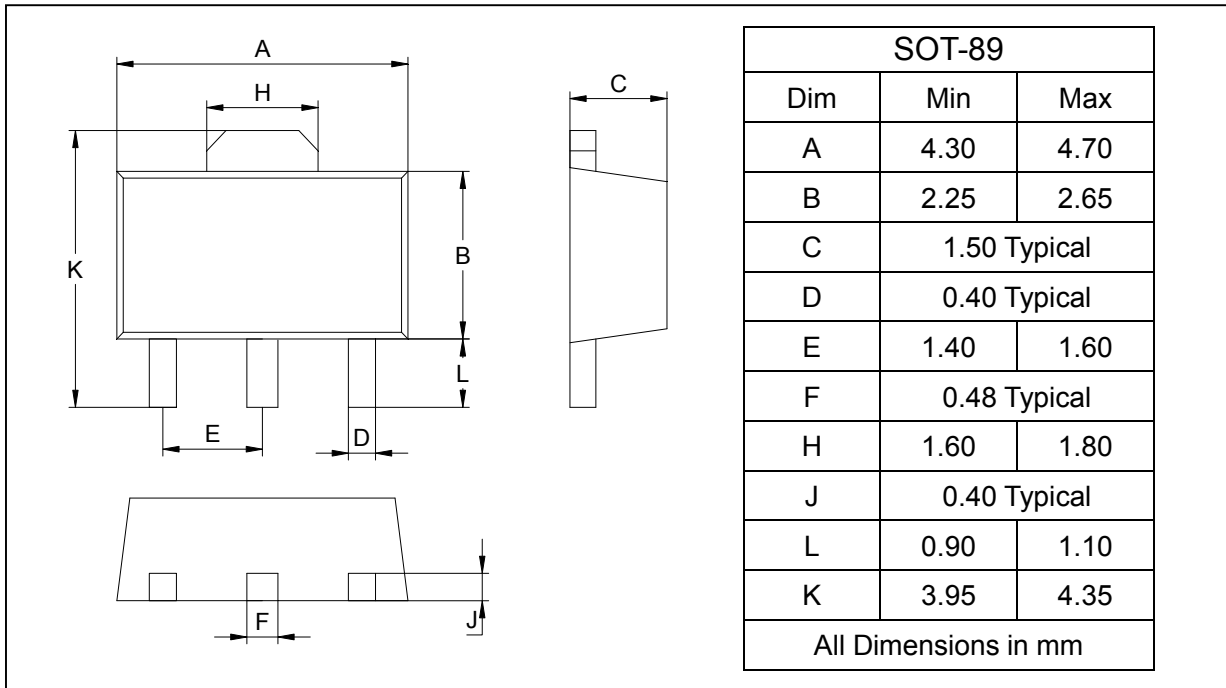
PNP Epitaxial Planar Silicon Transistors

2SB1119

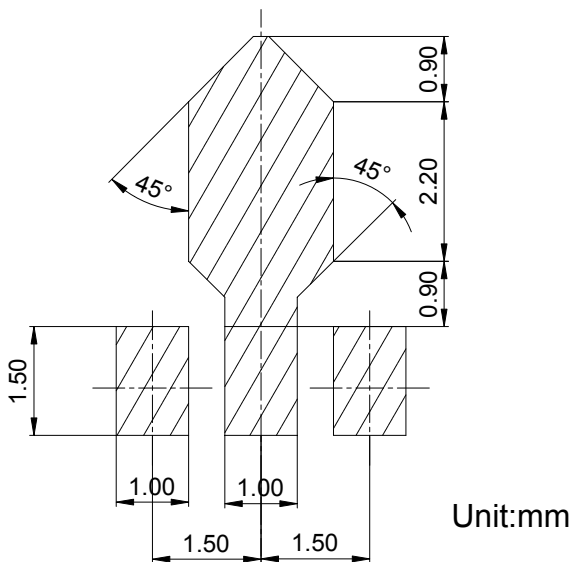
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SB1119	SOT-89	1000/Tape&Reel